

1. Product profile

1.1 Description

N-channel enhancement mode field-effect power transistor in a plastic package using Philips High-Performance Automotive TrenchMOS™ technology.

Product availability:

BUK9506-75B in SOT78 (TO-220AB)

BUK9606-75B in SOT404 (D²-PAK).

1.2 Features

- Very low on-state resistance
- 175 °C rated
- Q101 compliant
- Logic level compatible.

1.3 Applications

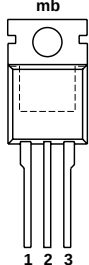
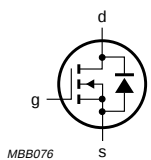
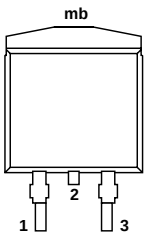
- Automotive systems
- Motors, lamps and solenoids
- 12 V, 24 V, and 42 V loads
- General purpose power switching.

1.4 Quick reference data

- $E_{DS(AL)S} \leq 852 \text{ mJ}$
- $I_D \leq 75 \text{ A}$
- $R_{DSon} = 5.2 \text{ m}\Omega$ (typ)
- $P_{tot} \leq 300 \text{ W}$.

2. Pinning information

Table 1: Pinning - SOT78 and SOT404 simplified outlines and symbol

Pin	Description	Simplified outline	Symbol
1	gate (g)	 MBK106	 MBB076
2	drain (d) [1]		
3	source (s)		
mb	mounting base, connected to drain (d)		
		 MBK116	
		SOT78 (TO-220AB)	SOT404 (D ² -PAK)

[1] It is not possible to make connection to pin 2 of the SOT404 package.

3. Limiting values

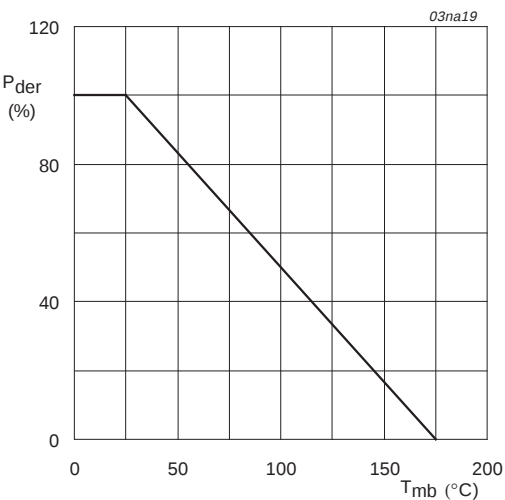
Table 2: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)		-	75	V
V_{DGR}	drain-gate voltage (DC)	$R_{GS} = 20 \text{ k}\Omega$	-	75	V
V_{GS}	gate-source voltage (DC)		-	± 15	V
I_D	drain current (DC)	$T_{mb} = 25 \text{ }^\circ\text{C}$; $V_{GS} = 5 \text{ V}$; Figure 2 and 3	[1] -	153	A
			[2] -	75	A
		$T_{mb} = 100 \text{ }^\circ\text{C}$; $V_{GS} = 5 \text{ V}$; Figure 2	[2] -	75	A
I_{DM}	peak drain current	$T_{mb} = 25 \text{ }^\circ\text{C}$; pulsed; $t_p \leq 10 \text{ }\mu\text{s}$; Figure 3	-	612	A
P_{tot}	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$; Figure 1	-	300	W
T_{stg}	storage temperature		-55	+175	$^\circ\text{C}$
T_j	junction temperature		-55	+175	$^\circ\text{C}$
Source-drain diode					
I_{DR}	reverse drain current (DC)	$T_{mb} = 25 \text{ }^\circ\text{C}$	[1] -	153	A
			[2] -	75	A
I_{DRM}	peak reverse drain current	$T_{mb} = 25 \text{ }^\circ\text{C}$; pulsed; $t_p \leq 10 \text{ }\mu\text{s}$	-	612	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	unclamped inductive load; $I_D = 75 \text{ A}$; $V_{DS} \leq 75 \text{ V}$; $V_{GS} = 5 \text{ V}$; $R_{GS} = 50 \text{ }\Omega$; starting $T_{mb} = 25 \text{ }^\circ\text{C}$	-	852	mJ

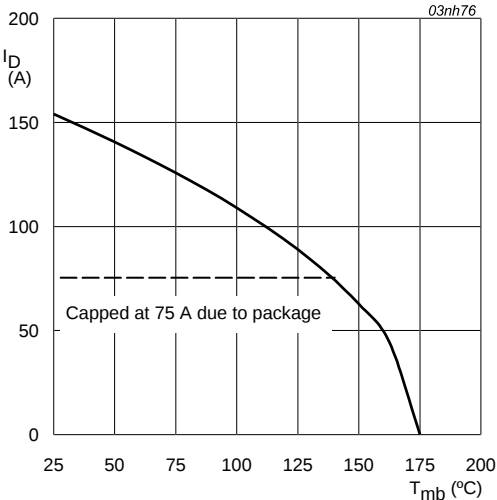
[1] Current is limited by power dissipation chip rating

[2] Continuous current is limited by package



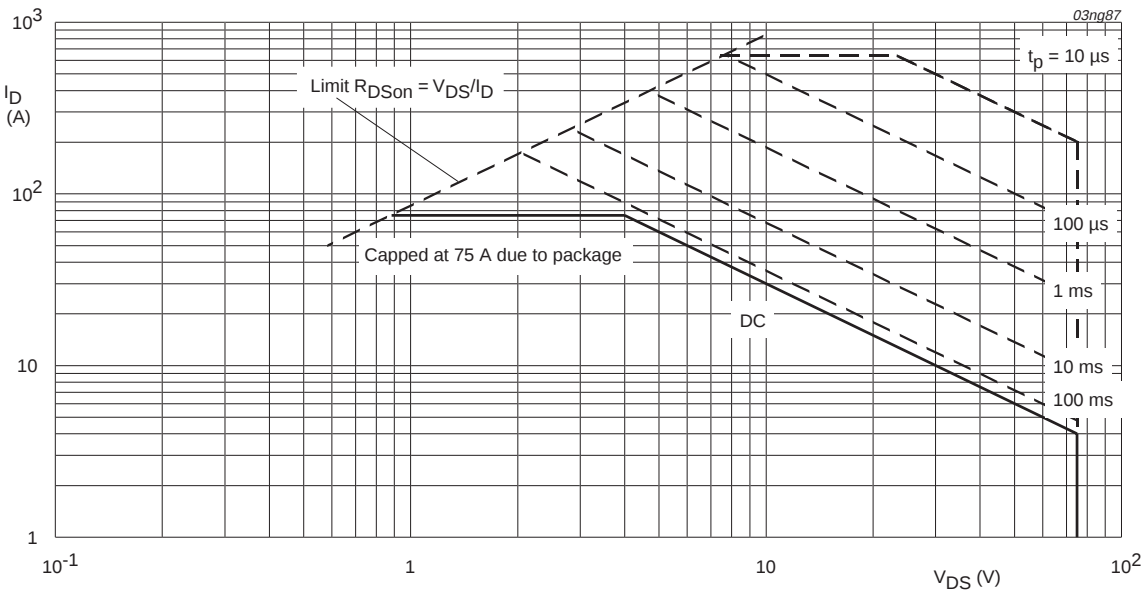
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of mounting base temperature.



$V_{GS} \geq 5$ V

Fig 2. Continuous drain current as a function of mounting base temperature.



$T_{mb} = 25$ °C; I_{DM} single pulse.

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

4. Thermal characteristics

Table 3: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Figure 4	-	-	0.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient					
	SOT78	vertical in still air	-	60	-	K/W
	SOT404	mounted on a printed circuit board; minimum footprint	-	50	-	K/W

4.1 Transient thermal impedance

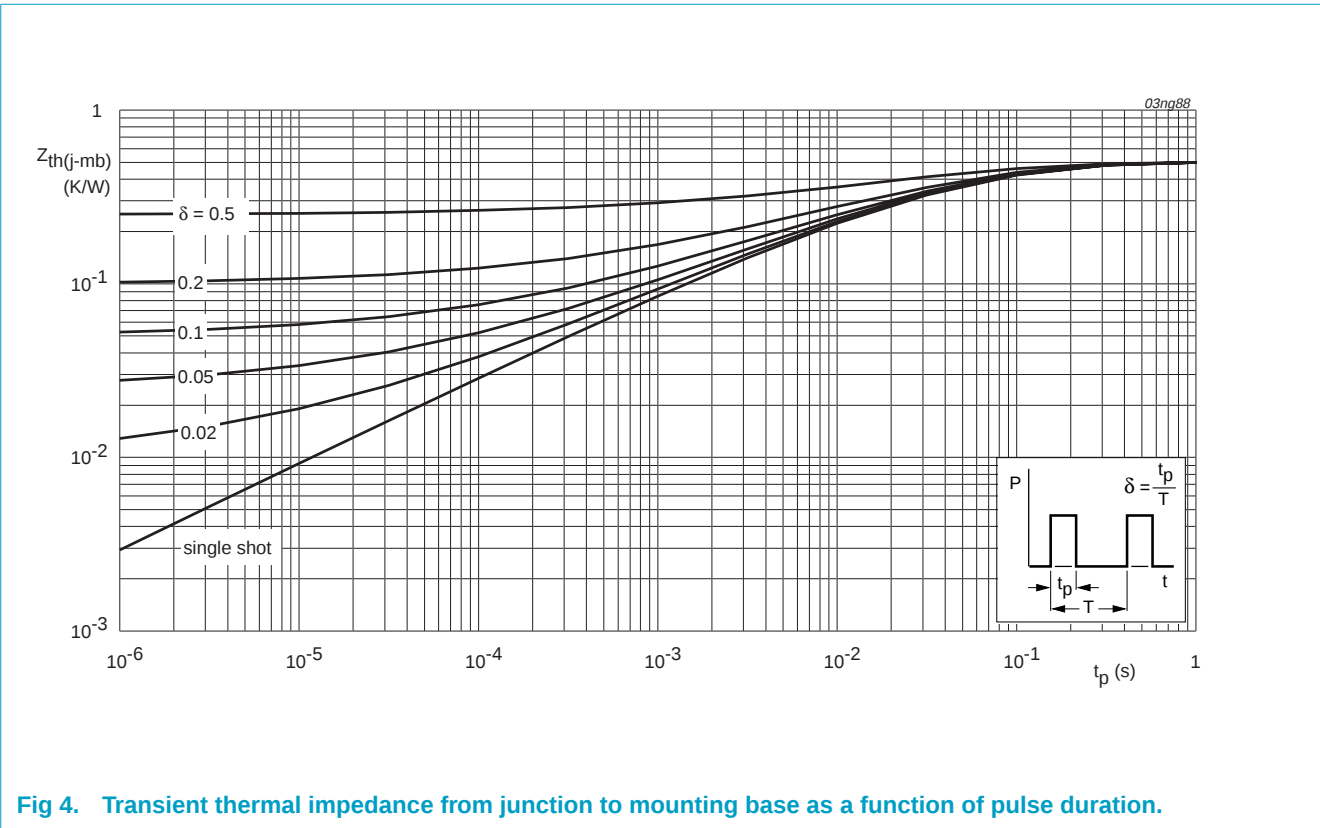


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration.

5. Characteristics

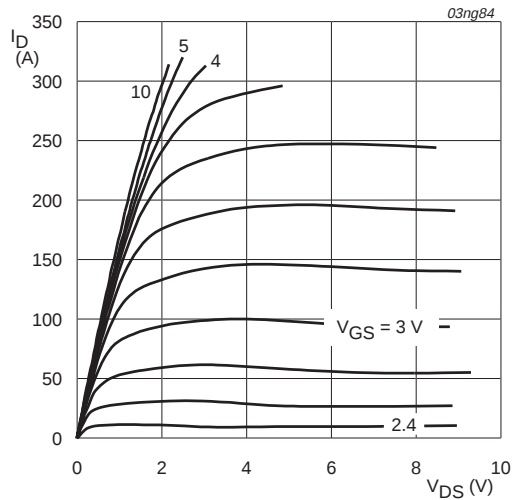
Table 4: Characteristics

$T_j = 25\text{ °C}$ unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 0.25 mA; V _{GS} = 0 V				
		T _J = 25 °C	75	-	-	V
		T _J = −55 °C	70	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; Figure 9				
		T _J = 25 °C	1.1	1.5	2	V
		T _J = 175 °C	0.5	-	-	V
		T _J = −55 °C	-	-	2.3	V
I _{DSS}	drain-source leakage current	V _{DS} = 75 V; V _{GS} = 0 V				
		T _J = 25 °C	-	0.02	1	μA
		T _J = 175 °C	-	-	500	μA
I _{GSS}	gate-source leakage current	V _{GS} = ±15 V; V _{DS} = 0 V	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 25 A; Figure 7 and 8				
		T _J = 25 °C	-	5.2	6.1	mΩ
		T _J = 175 °C	-	-	12.8	mΩ
		V _{GS} = 4.5 V; I _D = 25 A	-	-	6.6	mΩ
		V _{GS} = 10 V; I _D = 25 A	-	4.7	5.5	mΩ
Dynamic characteristics						
Q _{g(tot)}	total gate charge	V _{GS} = 5 V; V _{DD} = 60 V;	-	95	-	nC
Q _{gs}	gate-to-source charge	I _D = 25 A; Figure 14	-	17	-	nC
Q _{gd}	gate-to-drain (Miller) charge		-	37	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V;	-	8770	11693	pF
C _{oss}	output capacitance	f = 1 MHz; Figure 12	-	842	1010	pF
C _{rss}	reverse transfer capacitance		-	336	460	pF
t _{d(on)}	turn-on delay time	V _{DD} = 30 V; R _L = 1.2 Ω;	-	68	-	ns
t _r	rise time	V _{GS} = 5 V; R _G = 10 Ω	-	144	-	ns
t _{d(off)}	turn-off delay time		-	273	-	ns
t _f	fall time		-	116	-	ns
L _d	internal drain inductance	from drain lead 6 mm from package to centre of die	-	4.5	-	nH
		from contact screw on mounting base to centre of die SOT78	-	3.5	-	nH
		from upper edge of drain mounting base to centre of die SOT404	-	2.5	-	nH
L _s	internal source inductance	from source lead to source bond pad	-	7.5	-	nH

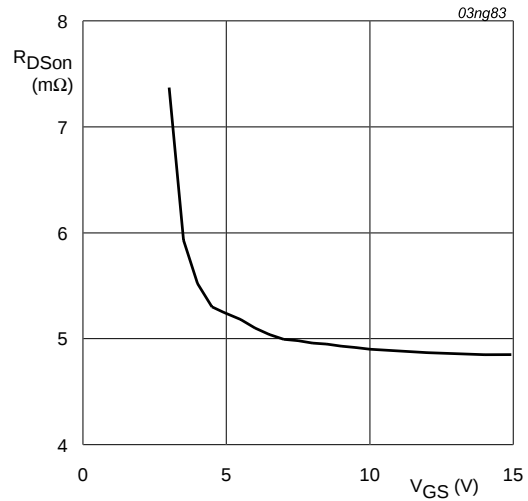
Table 4: Characteristics...continued
T_j = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V _{SD}	source-drain (diode forward) voltage	I _S = 40 A; V _{GS} = 0 V; Figure 15	-	0.85	1.2	V
t _{rr}	reverse recovery time	I _S = 20 A; dI _S /dt = -100 A/μs	-	68	-	ns
Q _r	recovered charge	V _{GS} = -10 V; V _{DS} = 30 V	-	176	-	nC



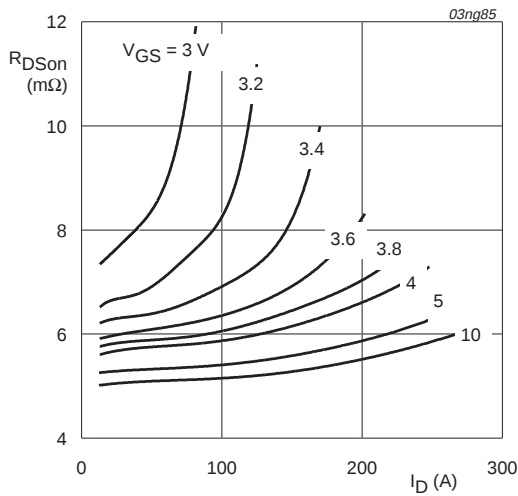
$T_j = 25^\circ\text{C}$; $t_p = 300 \mu\text{s}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



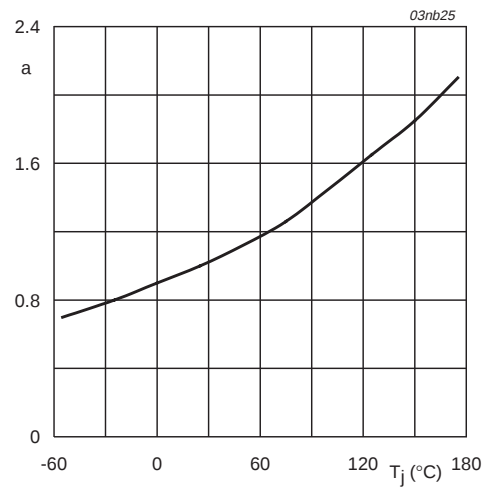
$T_j = 25^\circ\text{C}$; $I_D = 25 \text{ A}$

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values.



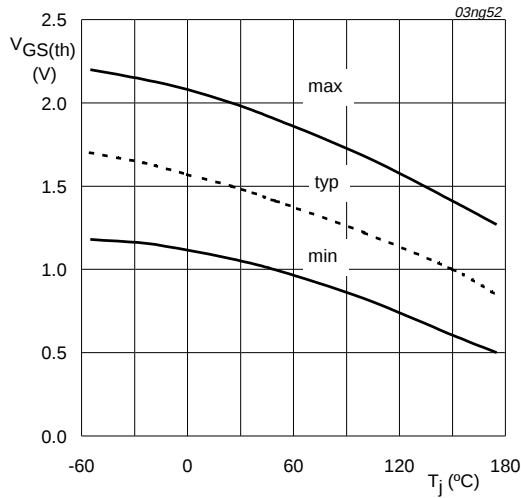
$T_j = 25^\circ\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



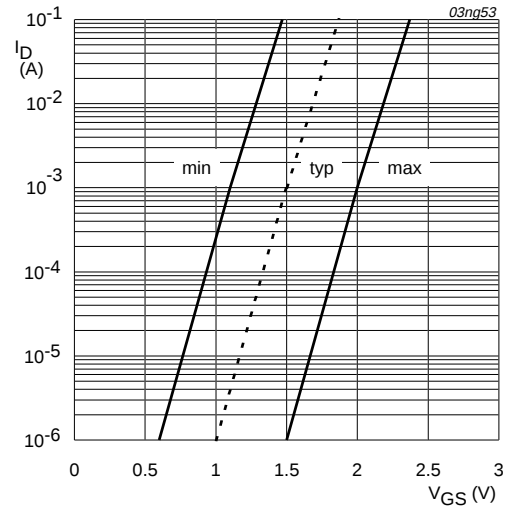
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.



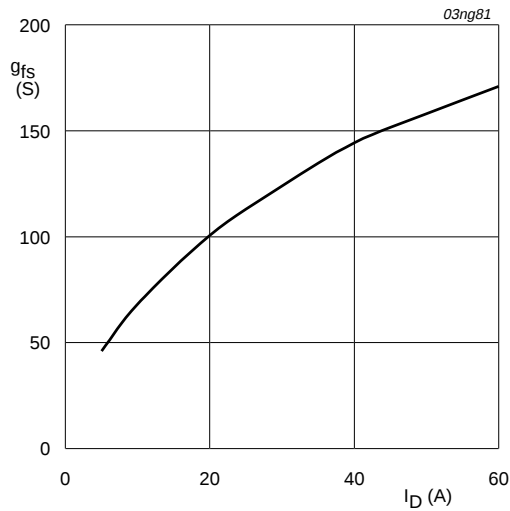
$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



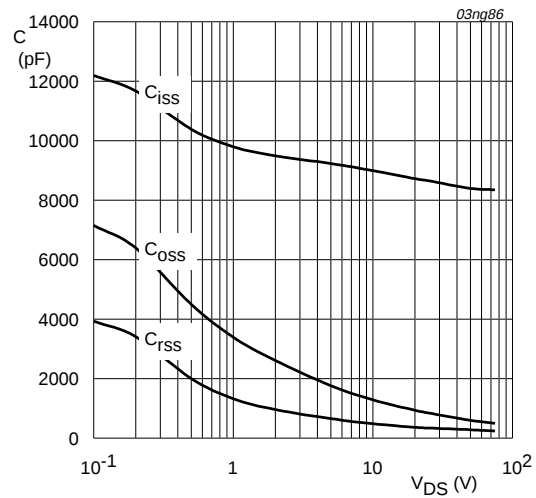
$T_j = 25 \text{ °C}$; $V_{DS} = V_{GS}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



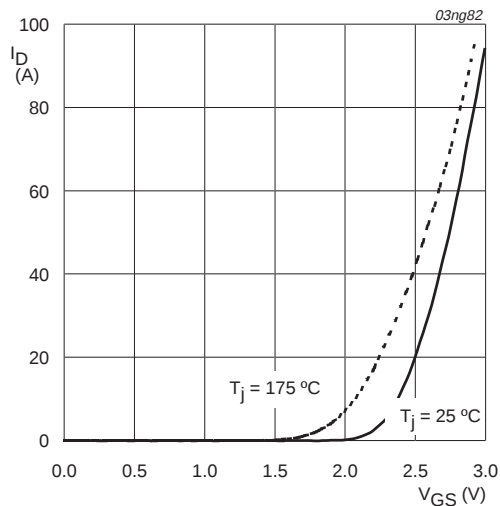
$T_j = 25 \text{ °C}$; $V_{DS} = 25 \text{ V}$

Fig 11. Forward transconductance as a function of drain current; typical values.



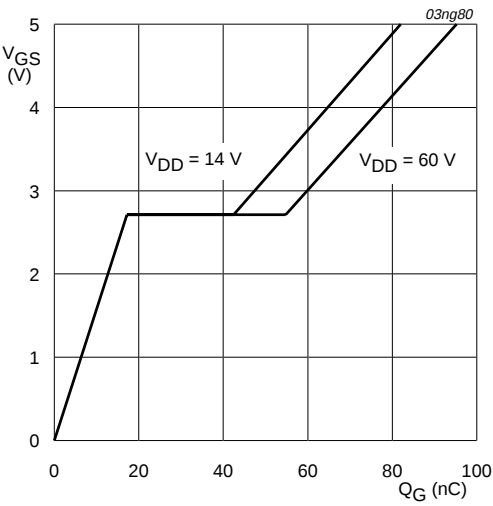
$V_{GS} = 0 \text{ V}$; $f = 1 \text{ MHz}$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



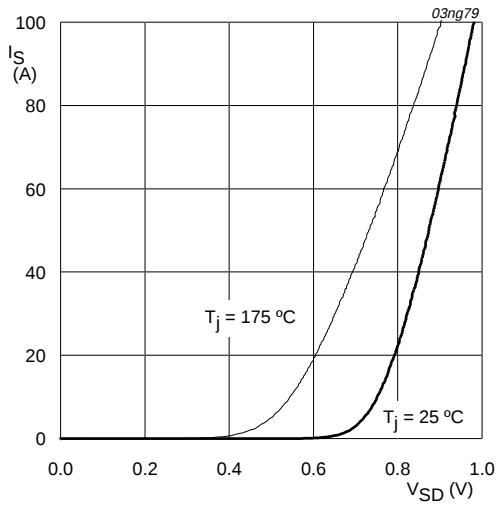
$V_{DS} = 25\text{ V}$

Fig 13. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



$T_j = 25\text{ °C}; I_D = 25\text{ A}$

Fig 14. Gate-source voltage as a function of turn-on gate charge; typical values.



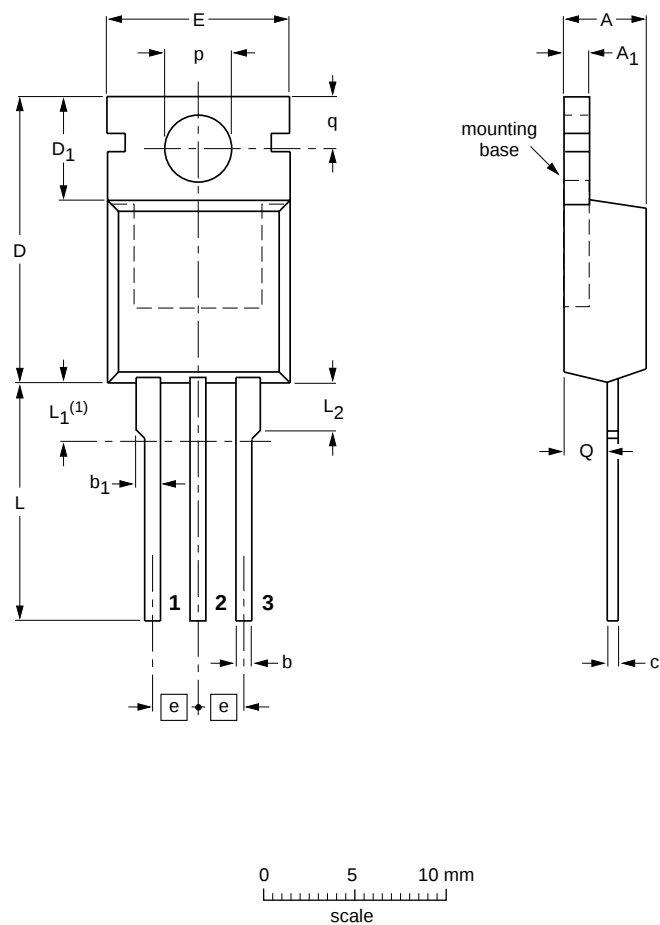
$V_{GS} = 0\text{ V}$

Fig 15. Reverse diode current as a function of reverse diode voltage; typical values.

6. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	b ₁	c	D	D ₁	E	e	L	L ₁ ⁽¹⁾	L ₂ max.	p	q	Q
mm	4.5 4.1	1.39 1.27	0.9 0.7	1.3 1.0	0.7 0.4	15.8 15.2	6.4 5.9	10.3 9.7	2.54	15.0 13.5	3.30 2.79	3.0	3.8 3.6	3.0 2.7	2.6 2.2

Note

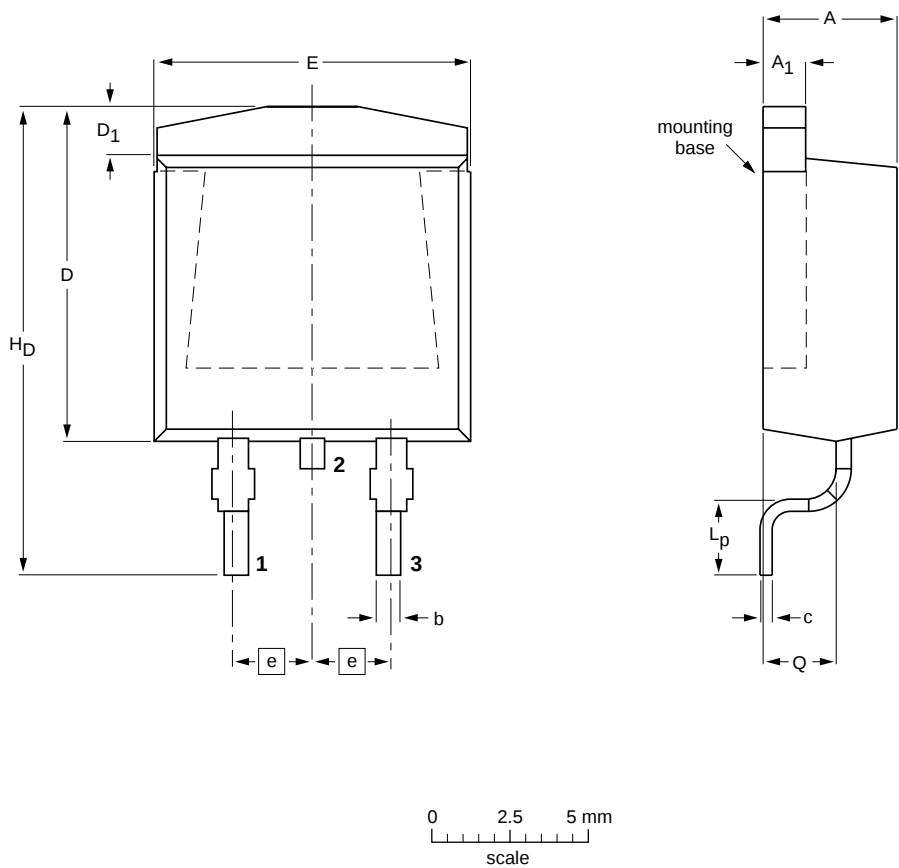
1. Terminals in this zone are not tinned.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT78		3-lead TO-220AB	SC-46			00-09-07 01-02-16

Fig 16. SOT78 (TO-220AB).

Plastic single-ended surface mounted package (Philips version of D²-PAK); 3 leads
(one lead cropped)

SOT404



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁	b	c	D _{max.}	D ₁	E	e	L _p	H _D	Q
mm	4.50 4.10	1.40 1.27	0.85 0.60	0.64 0.46	11	1.60 1.20	10.30 9.70	2.54	2.90 2.10	15.80 14.80	2.60 2.20

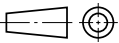
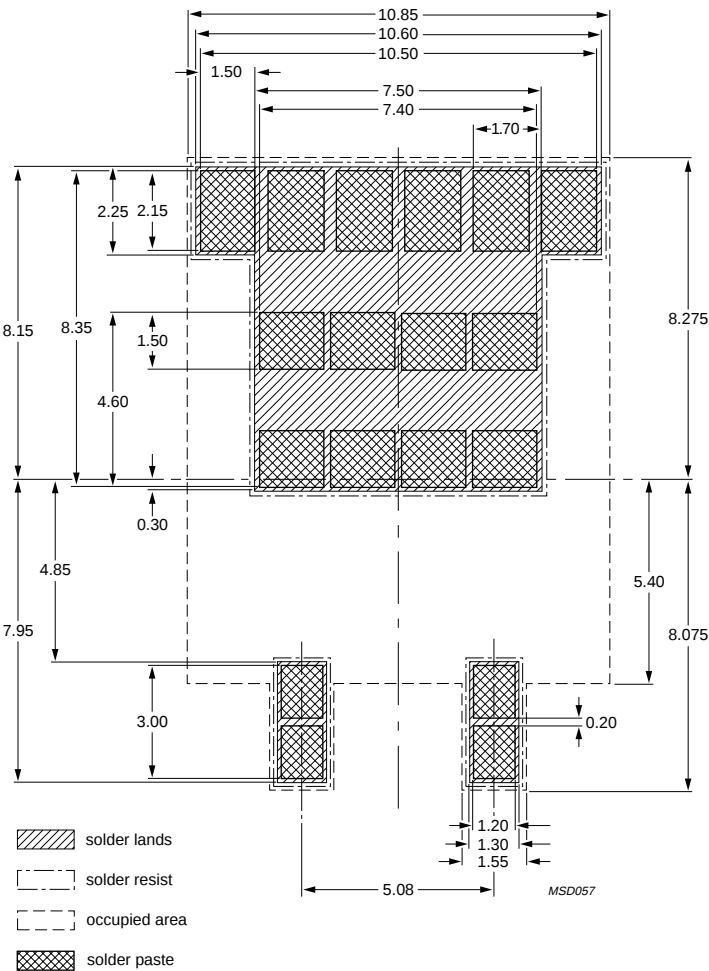
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT404						-99-06-25 01-02-12

Fig 17. SOT404 (D²-PAK)

7. Soldering



Dimensions in mm.

Fig 18. Reflow soldering footprint for SOT404.

8. Revision history

Table 5: Revision history

Rev	Date	CPCN	Description
02	20020930	-	Product data (9397 750 10279) Modifications: Description in Section 1 changed from: N-channel enhancement mode field-effect power transistor in a plastic package using generation three TrenchMOS™ technology, featuring very low on-state resistance. to: N-channel enhancement mode field-effect power transistor in a plastic package using Philips High-Performance Automotive TrenchMOS™ technology.
01	20020405	-	Product data (9397 750 09495)

9. Data sheet status

Data sheet status ^[1]	Product status ^[2]	Definition
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

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Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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